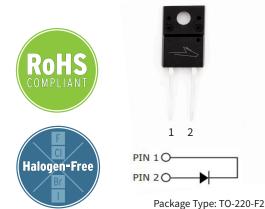


3rd Generation 600 V, 6 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Marking: C3D06060

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Features

- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- **Fully Isolated Case**
- **Extremely Fast Switching**

Applications

- Switch Mode Power Supplies (SMPS)
- Free Wheeling Diodes in Inverter Stages
- Boost for PFC & DC-DC Stages
- Solar Inverters
- AC/DC Converters

Maximum Ratings (T_c = 25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes	
Repetitive Peak Reverse Voltage	V _{RRM}	600	V			
DC Blocking Voltage	V _{DC}	600	V			
		11.5		T _c = 25 °C	E' 2	
Continuous Forward Current	I _F	6		T _c = 125 °C	Fig. 3	
		4		T _c = 150 °C		
Repetitive Peak Forward Surge		22		$T_c = 25 ^{\circ}\text{C}$, $t_p = 10 \text{ms}$, Half Sine Wave		
Current	FRM	15	Α	$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms}, \text{Half Sine Wave}$		
Non-Repetitive Forward Surge Current	I _{FSM}	44		$T_c = 25$ °C, $t_p = 10$ ms, Half Sine Wave	Fig. 8	
		41		T _c = 110 °C,t _p = 10 ms, Half Sine Wave		
Non-Repetitive Peak Forward		540		$T_{c} = 25 {}^{\circ}\text{C}, t_{p} = 10 \mu\text{s}, \text{Pulse}$	F: 0	
Surge Current	F,Max	460		$T_{c} = 110^{\circ}C, t_{p} = 10 \mu s, Pulse$	Fig 8.	
D D'	<u></u>	37	14/	T _c = 25 °C	F' . 4	
Power Dissipation	P _{tot}	16	W	T _c = 110 °C	Fig. 4	
Diode dV/dt Ruggedness	dV/dt	200	V/ns	V _R = 0-600V		
i²t value (Per Leg)	∫i²dt	9.6	A ² s	$T_c = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$		
		8.4		$T_{c} = 110 {}^{\circ}\text{C}, t_{p} = 10 {}^{\circ}\text{ms}$		

Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes
Forward Voltage		1.5	1.7	V	I _F = 6 A, T _j = 25 °C	Fig. 1
	V _F	2.0	2.4		I _F = 6 A, T _j = 175 °C	
Reverse Current		6.5	33	μА	$V_R = 600 \text{ V}, T_j = 25 \text{ °C}$	Fig. 2
	I _R	13	132		$V_R = 600 \text{ V}, T_j = 175 \text{ °C}$	
Total Capacitive Charge	Q _c	15		nC	$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, I_F = 6 \text{ A}$	Fig. 5
		295			$V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Total Capacitance	c	28.5		pF	$V_R = 200 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	Fig. 6
		25.5			$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E _c	2.3		μJ	V _R = 400 V	Fig. 7

Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

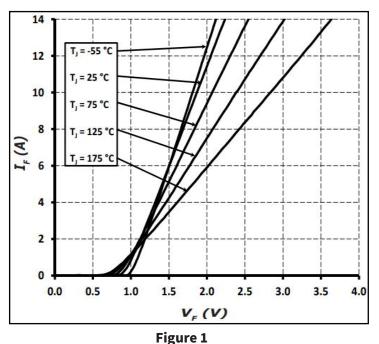
Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R _{0, JC (TYP)}	4.0	°C/W	
Junction Temperature	T _j	-55 to +175	۰٫	
Case & Storage Temperature	T _c	-55 to +175		
TO 220 Mounting Toyana		1	Nm	M3 Screw
TO-220 Mounting Torque	-	8.8	lbf-in	6-32 Screw

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Notes
Human Body Model	НВМ	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

Typical Performance



Forward Characteristics

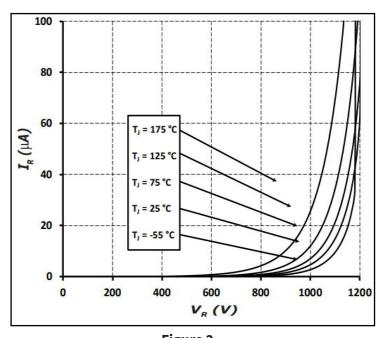
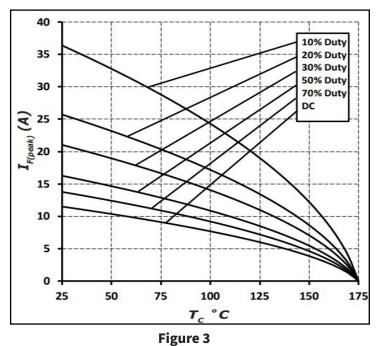


Figure 2Reverse Characteristics



Current Derating

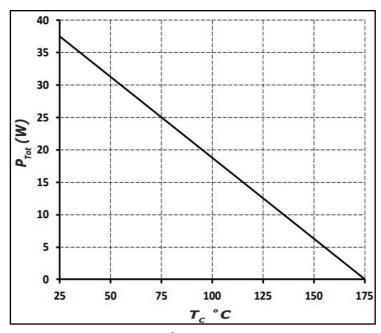
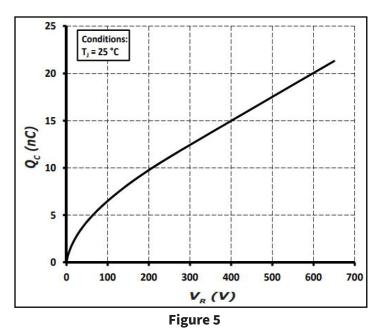
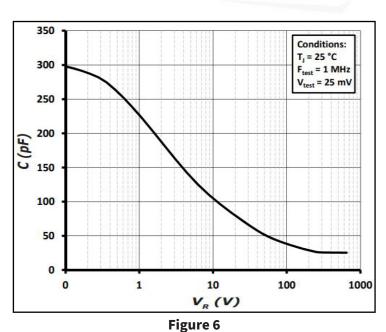


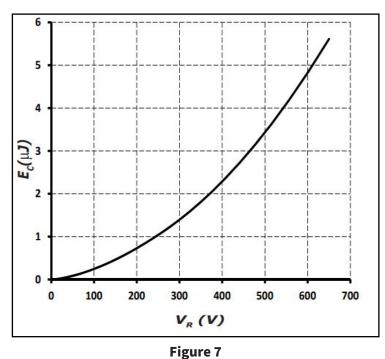
Figure 4Power Derating



Total Capacitance vs. Reverse Voltage



Capacitace vs. Reverse Voltage



Capacitance Stored Energy

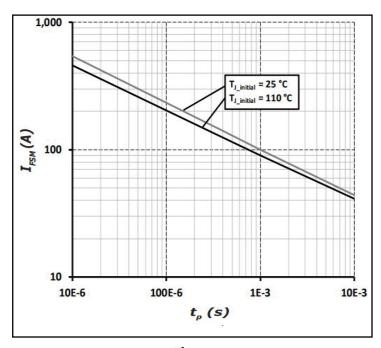


Figure 8Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

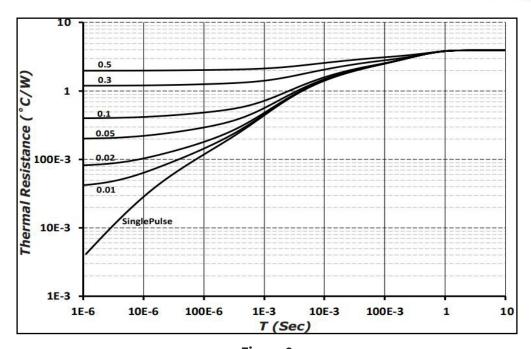
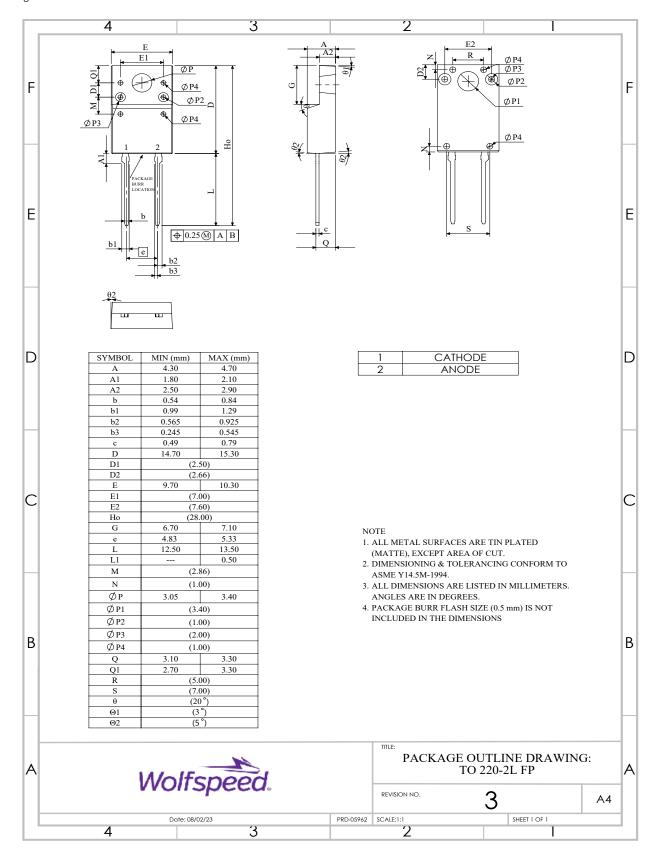


Figure 9Transient Thermal Impedance

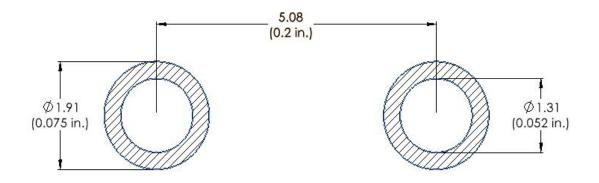
Package Dimensions & Pin-Out

Package: TO-220-F2



Recommended Solder Pad Layout

Primary dimensions shown in mm.



Product Ordering Information

Order Number	Packing Type	
C3D06060F	Tube	

Revision History

Document Version	Date of Release	Description of Changes
F	February- 2019	Initial Release
7	October-2023	Update Package Drawing Update Landing Pad Updated Branding Updated Package Image
8	November-2023	Corrected POD A1,b1, and Q

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